

SPECIFICATION AMENDMENTS

In the Abstract on Page 16, beginning on Line 6, please make the following amendments:

A method of manufacturing an on-chip A-transformer balun is obtained that is symmetrical in structure, provides high current, or high voltage, amplification and has high coupling coefficients while maintaining minimal overall size. The balun structure includes primary and secondary metal windings at separate layer interfaces. The primary and secondary metal windings are symmetrical and can have any number of turns, which is only limited by integrated circuit area and capacitance. Accordingly, the primary and secondary windings may be on as many layers as needed. Further, the primary and/or secondary may include a center tap ground, which enables the winding to be used as a differential port. includes creating, on a semiconductor substrate, a primary winding having at least one substantially symmetrical primary turn on a first dielectric layer and at least one metal bridge on a second layer. A secondary winding is created on the semiconductor substrate, the secondary winding having at least one substantially symmetrical secondary turn on a third dielectric layer and at least one metal bridge on a fourth dielectric layer. In an alternative embodiment, the primary winding has at least one first primary turn on a first dielectric layer and at least one second primary turn on a second dielectric layer and at least one via that operably connects the first primary turn to the second primary turn. The secondary winding has at least one first secondary turn on a third dielectric layer and at least one second secondary turn on a fourth dielectric layer.